

TABLE 8 : NPN/PNP SUPER E-LINE TYPES

These devices offer the ultimate performance for TO-92 style package. They have been designed to operate and provide useful gain at current levels up to 6A with power dissipation capabilities in excess of 1W at 25°C ambient temperature.

Type	V _{CBO} V	V _{CEO} V	Max. cont. I _C A	Max. I _{CM} A	Max. V _{at} V _{CE(sat)}			h _{FE} at		Min. f _T at		P _{tot} at T _{amb} = 25°C mW	Complement
					V	I _C A	I _B A	Min.	I _C A	MHz	I _C mA		
NPN													
ZTX653§	120	100	2	6	0.5	2	0.2	25	2	140	100	1000	ZTX753
ZTX652	100	80	2	6	0.5	2	0.2	25	2	140	100	1000	ZTX752
ZTX651§	80	60	2	6	0.5	2	0.2	40	2	140	100	1000	ZTX751
ZTX650	60	45	2	6	0.5	2	0.2	40	2	140	100	1000	ZTX750
ZTX649§	35	25	2	6	0.5	2	0.2	75	2	150	100	1000	ZTX749
PNP													
ZTX753§	120	100	2	6	0.5	2	0.2	25	2	100	100	1000	ZTX653
ZTX752	100	80	2	6	0.5	2	0.2	25	2	100	100	1000	ZTX652
ZTX751§	80	60	2	6	0.5	2	0.2	40	2	100	100	1000	ZTX651
ZTX750	60	45	2	6	0.5	2	0.2	40	2	100	100	1000	ZTX650
ZTX749§	35	25	2	6	0.5	2	0.2	75	2	100	100	1000	ZTX649

TABLE 9 : NPN HIGH GAIN SUPER E-LINE

A range of high gain, high performance, medium power devices designed to replace Darlington transistors in applications where low saturation voltages are required. Ideally suited for battery-driven applications.

Type	V_{CBO} V_{CEO} V	Max. cont I_C A	Max. I_{CM} A	Max. $V_{CE(sat)}$ at			h_{FE} at		Min. f_T at		P_{tot} at $T_{amb} = 25^\circ C$ mW
				V	I_C mA	I_B mA	Min.	I_C mA	MHz	I_C mA	
ZTX694B	120	0.5	1	0.5	400	5	400	200	150	50	1000
ZTX692B	70	1	2	0.5	1000	10	400	500	150	50	1000
ZTX690B	45	2	6	0.5	2000	40	400	1000	150	50	1000
ZTX689B	20	2	6	0.5	2000	10	400	2000	150	50	1000

§Also available with centre collector lead form option. See centre collector section for details.